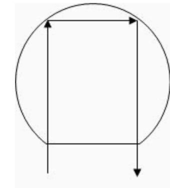
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	400.00 +/- 13.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<50.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<50.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Global Flatness (TIR)	< 3 um	20mmx20mm sites, no partials
	11.0	Edge Exclusion	7mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	109.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	1 - 10 Ohm cm	Wafer Vendor
	18.0	Backside Finish	Polished with lasermark	Wafer Vendor
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Grown on handle and/or device silicon	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	24.0	Nominal Thickness	290.00 +/- 2.00 µm	ADE Single Point, 100%
	25.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phos	Wafer Vendor
	28.0	Device Resistivity	1 - 10 Ohm-cm	Wafer Vendor
	29.0	Oxygen Concentration	<8E17 cm-3	Wafer Vendor
	30.0	Carbon Concentration	<2E16 cm-3	Wafer Vendor
	31.0	Voids	0	Bright Light, 100% (note 2)
	32.0	Scratches	<25mm Total Length	Bright Light, 100% (note 2)
	33.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

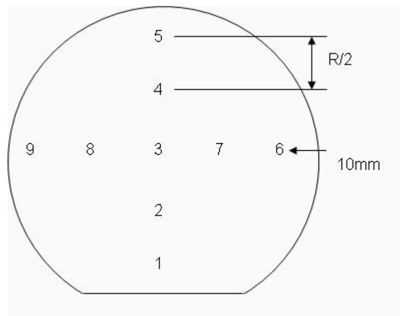
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information